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(71) Applicant (for all designated States except US): INTERNATIONAL BUSINESS MACHINES CORPORATION [US/US]; New Orchard Road, Armonk, NJ 10504 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **DOKUMACI, Omer, H.** [TR/US]; 32E Wintrop Court, Wappingers Falls, NY 12590 (US). **RONSHHEIM, Paul** [US/US]; 118 Hollyberry Drive, Hopewell Junction, NY 12533 (US).

(74) Agent: **PEPPER, Margaret, A.**; International Business Machines Corporation, 2070 Route 53, Hopewell Junction, NY 12533 (US).

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(54) Title: METHOD FOR FORMING NON-AMORPHOUS, ULTRA-THIN SEMICONDUCTOR DEVICES USING SACRIFICIAL IMPLANTATION LAYER

(57) Abstract: A method for forming a semiconductor device includes defining a sacrificial layer (108) over a single crystalline substrate (106). The sacrificial layer (108) is implanted with a dopant species in a manner that prevents the single crystalline substrate (106) from becoming substantially amorphized. The sacrificial layer (108) is annealed so as to drive said dopant species from said sacrificial layer (108) into said single crystalline substrate (106).